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Bryan S. Kasprowicz
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Bryan S. Kasprowicz, Photronics, Inc. (United States)

2 Invited Session: Joint with Photomask and Scanning Microscopies
Naoya Hayashi, Dai Nippon Printing Company, Ltd. (Japan)
Bryan S. Kasprowicz, Photronics, Inc. (United States)
Michael T. Postek, National Institute of Standards and Technology (United States)

3 Edge Placement Error Issue and Solution for Multi-Patterning
Peter D. Buck, Mentor Graphics Corporation (United States)
Aki Fujimura, D2S, Inc. (United States)

4 EUV Mask Infrastructure Readiness
Emily E. Gallagher, IMEC (Belgium)
Thomas B. Faure, GLOBALFOUNDRIES Inc. (United States)

5 Student Session
Bryan S. Kasprowicz, Photronics, Inc. (United States)
Jim N. Wiley, ASML US, Inc. (United States)
Thomas Scheruebl, Carl Zeiss SMT GmbH (Germany)

6 Scanning Beam Technologies and Applications: Joint Session with Photomask and Scanning Microscopies
Michael T. Postek, National Institute of Standards and Technology (United States)
Jan Hendrik Peters, Carl Zeiss SMS GmbH (Germany)

7 EUV Simulation
Paul C. Allen, Toppan Photomasks, Inc. (United States)
Banqiu Wu, Applied Materials, Inc. (United States)

8 Photomask Technology for Alternative Lithography: NIL
Douglas J. Resnick, Canon Nanotechnologies, Inc. (United States)
Uwe Dietze, SUSS MicroTec Inc. (United States)

9 Mask Data Preparation and Mask Process Correction
Bala Thumma, Synopsys, Inc. (United States)
Linyong Pang, D2S, Inc. (United States)

10 Invited and Best Papers
Uwe F. W. Behringer, UBC Microelectronics (Germany)
Brian J. Grenon, Grenon Consulting, Inc. (United States)

11 Metrology and Inspection
Mark M. Wylie, KLA-Tencor Idaho (United States)
Jerry Cullins, HOYA Corporation (Japan)

12 Patterning and Process
Kenichi Saito, NuFlare Technology, Inc. (Japan)
Russell B. Cinque, JEOL USA Inc. (United States)